L Number	Hits	Search Text	DB	Time stamp
387	871	(438/238).CCLS.	USPAT; US-PGPUB;	2003/12/09 09:42
			EPO; JPO;	
			DERWENT;	!
			IBM TDB	
388	269	((438/238).CCLS.) and (SRAM or(static near	USPAT;	: 2003/12/09 09:12
;		random near access near memory))	US-PGPUB	
	269	((438/238).CCLS.) and (SRAM or(static near	USPAT;	2003/12/09 09:13
		random near access near memory))	US-PGPUB;	
			EPO; JPO;	!
			DERWENT;	:
	2	·	IBM_TDB	1 2022 /12 /22 22 22
390 391	3 774	("5330930"   "5365104"   "5877059").PN. (257/903).CCLS.	USPAT;	2003/12/09 09:28 2003/12/09 09:45
	114	(237/303).0013.	US-PGPUB;	2003/12/03 03.43
			EPO; JPO;	•
			DERWENT;	İ
!			IBM TDB	ļ
- '	31345	SRAM (static near random near access near	USPAT;	2003/12/09 09:12
		memory)	US-PGPUB	İ
_	26244	(SRAM (static near random near access near	USPAT;	2003/12/08 14:13
	0.0000	memory) ) and (trench via contact open\$)	US-PGPUB	1 2002 /10 /20 14 11
-	26208		USPAT;	2003/12/08 14:14
_	5020	memory) ) and (trench via contact open\$3) ((SRAM (static near random near access	US-PGPUB USPAT;	2003/12/08 14:15
- i	3920	near memory) ) and (trench via contact	US-PGPUB	2003/12/08 14:13
		open\$3)) and etch\$3	OD EGEOD	į
_	4948		USPAT;	2003/12/08 14:15
		near memory) ) and (trench via contact	US-PGPUB	!
		open\$3)) and etch\$3) and (source drain)	!	
-	4059	((((SRAM (static near random near access	USPAT;	2003/12/08 14:16
		near memory) ) and (trench via contact	US-PGPUB	
		open\$3)) and etch\$3) and (source drain))	İ	
		and resist\$6		!
- !	3615	(((((SRAM (static near random near access	USPAT;	2003/12/08 14:16
		near memory) ) and (trench via contact	US-PGPUB	
		open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate	1	:
_	3349	. (((((SRAM (static near random near access	USPAT;	2003/12/08 14:17
	5515	near memory) ) and (trench via contact	US-PGPUB	
!		open\$3)) and etch\$3) and (source drain))		
		and resist\$6) and gate) and transistor		:
-	76	((((((SRAM (static near random near	USPAT;	2003/12/08 14:17
		access near memory) ) and (trench via	US-PGPUB	1
		contact open\$3)) and etch\$3) and (source	•	
		drain)) and resist\$6) and gate) and		
		transistor) and (horizontal near10		•
_	280	transistor) ·((((((SRAM (static near random near	USPAT;	; 2003/12/08 17:43
	200	access near memory) ) and (trench via	US-PGPUB	2003/12/00 17.43
		contact open\$3)) and etch\$3) and (source	35 13105	
		drain)) and resist\$6) and gate) and		!
		transistor) and ((pull?down (pull near3		
		down)) near10 transistor)		
	42124	SRAM (static near random near access near	USPAT;	2003/12/08 17:43
		memory)	US-PGPUB;	
- 			EPO; JPO;	!
			i contract of the contract of	
-   			DERWENT;	•
	202	/////CDDM /gtatio	DERWENT; IBM_TDB	2003/12/09 19:20
	283	((((((SRAM (static near random near	DERWENT; IBM_TDB USPAT;	2003/12/08 18:29
	283	access near memory) ) and (trench via	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/12/08 18:29
-	283	access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/08 18:29
-	283	access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/08 18:29
-	283	access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/08 18:29
-		access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/08 18:29
-		access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
-		access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	
-		access near memory) ) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	